

### IN THE CLAIMS

Please amended the following claims:

30. (currently amended) A semiconductor device comprising:  
a gate electrode formed on a gate dielectric formed on a substrate surface, the gate electrode having a first thickness;  
a gate silicon germanium film formed on the gate electrode, the gate silicon germanium film having a second thickness;  
a gate silicide layer formed on the gate silicon germanium film, the gate silicide layer having a third thickness;  
a pair of sidewall spacers on opposite sides of the gate electrode, the sidewall spacers having a height of at least  $200\text{\AA}$  above the third thickness of the gate silicide layer and a width of less than  $300\text{\AA}$ ;  
a pair of source and drain regions formed on opposite sides of said gate electrode, said source and drain regions having a silicon germanium film formed beneath said substrate surface and a pair of ultra shallow tip regions formed beneath the pair of sidewall spacers.
31. (original) The semiconductor device of claim 30, wherein the gate electrode is polysilicon.
32. (cancelled)
33. (previously presented) The semiconductor device of claim 30 further comprising:  
a silicide layer formed on the silicon germanium film of said source and drain regions.

34. (previously presented) The semiconductor device of claim 33 further comprising:

an isolation region having a top surface positioned below the top surface of the silicon germanium film of said source and drain regions.

35. (original) The semiconductor device of claim 33 further comprising:  
an isolation region having a top surface positioned below the silicide layer.

36 - 43 (cancelled)